polysilicon gate.

Please replace the paragraph beginning at page 6, line 5 with the following rewritten paragraph:

Specifically, when the dry surface treatment is implemented, two power supplies 302, 304 are separately provided to the argon and the heater 310 (also substrate electrode). The power provided to the substrate electrode 310 causes the substrate 300 to acquire a self-bias, and thereby accelerates argon ions from the target 310 toward the exposed substrate 300 and polysilicon gate. Thus, the exposed substrate 300 and polysilicon gate are subject to some bombardment by the argon ions 308 from the target 310. The argon is preferably provided with a bias of about 250W to about 450W from the first power supply 302, while the substrate 300 is preferably provided with a bias of about 150W to about 300W. 450W is an upper limit provided to a conventional IMP chamber, but the upper limit is variable according to the development of plasma equipment. By properly modifying the quantities of the RF power, the substrate bias and the substrate position (preferably on the heater), this dry surface treatment can be harnessed to simultaneously amorphize and clean the exposed substrate 300 and polysilicon gate.

Please replace the paragraph beginning at page 6, line 18 with the following rewritten paragraph:

In the description of the related art, the biases provided to the argon and to the substrate 300 are conventionally about 50-300W and 100-150W, respectively. Because the biases are provided only for dry cleaning, rather than for amorphization, they are substantially lower than the biases provided for dry cleaning as well as amorphization in the present invention. In other words, if the biases provided are substantially higher than the biases provided for only dry cleaning in the prior art, they are sufficient to dry clean as well as amorphize the exposed